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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I²C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f207vgt7

Table 10. Alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port A	PA0-WKUP	-	TIM2_CH1_ETR	TIM 5_CH1	TIM8_ETR	-	-		USART2_CTS	UART4_TX	-	-	ETH_MII_CRS	-	-	-	EVENTOUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-		USART2_RTS	UART4_RX	-	-	ETH_MII _RX_CLK ETH_RMII _REF_CLK	-	-	-	EVENTOUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-		USART2_TX	-	-	-	ETH_MDIO	-	-	-	EVENTOUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-		USART2_RX	-	-	OTG_HS_ULPI_D0	ETH _MII_COL	-	-	-	EVENTOUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK	-	-		-	OTG_HS_SOF	DCMI_HSYNC	-	EVENTOUT
	PA5	-	TIM2_CH1_ETR	-	TIM8_CH1N	-	SPI1_SCK	-	-	-	-	OTG_HS_ULPI_C K	-	-	-	-	EVENTOUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_PIXCK	-	EVENTOUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-	-	TIM14_CH1	-	ETH_MII _RX_DV ETH_RMII _CRS_DV	-	-	-	EVENTOUT
	PA8	MCO1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	-	-	EVENTOUT
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	-	-	USART1_TX	-	-		-	-	DCMI_D0	-	EVENTOUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	DCMI_D1	-	EVENTOUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	-	-	EVENTOUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS	-	CAN1_TX	OTG_FS_DP	-	-	-	-	EVENTOUT
	PA13	JTMS-SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA15	JTDI	TIM 2_CH1 TIM 2_ETR	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	-	-	-	-	-	-	-	-	EVENTOUT

5 Memory mapping

The memory map is shown in *Figure 16*.

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 1.8 V ≤V_{DD} ≤3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 17*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 18*.

Figure 17. Pin loading conditions

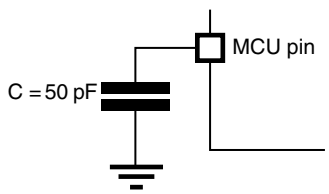


Figure 18. Pin input voltage

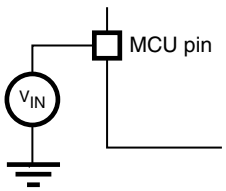
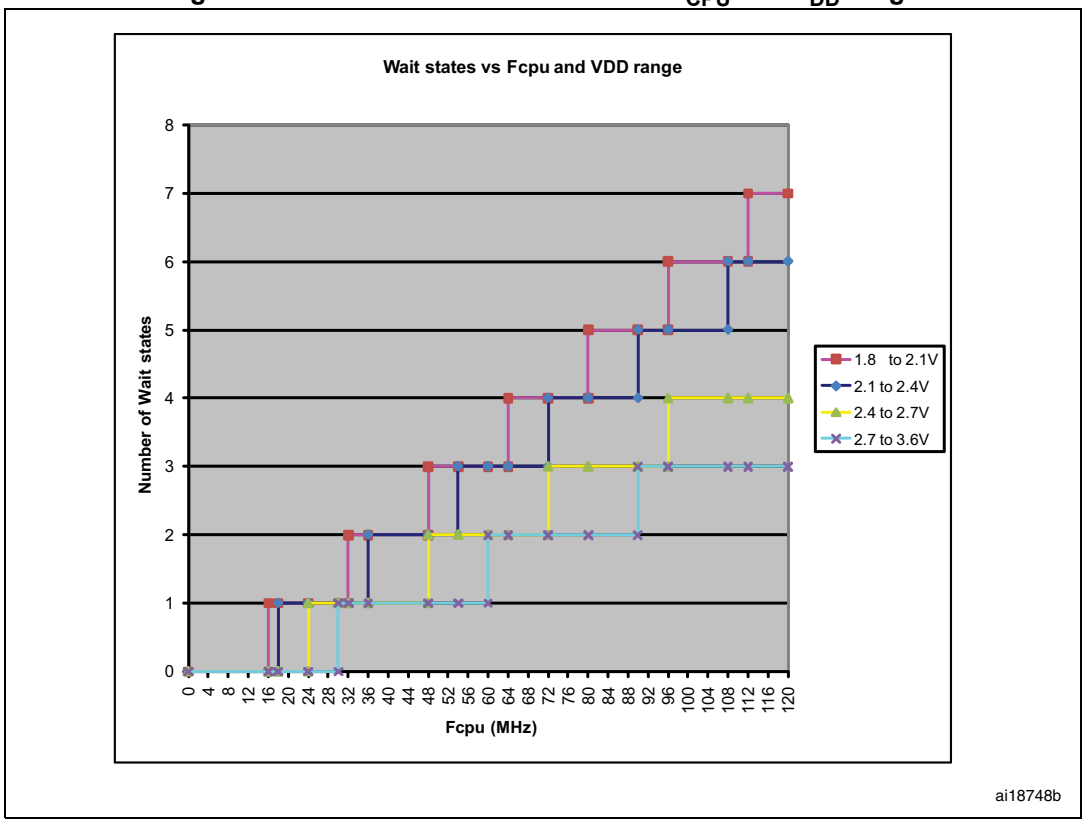


Table 15. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency ($f_{Flashmax}$)	Number of wait states at maximum CPU frequency (f_{CPUmax}= 120 MHz)(1)	I/O operation	FSMC_CLK frequency for synchronous accesses	Possible Flash memory operations
V_{DD} =1.8 to 2.1 V(2)	Conversion time up to 1 Msps	16 MHz with no Flash memory wait state	7(3)	– Degraded speed performance – No I/O compensation	Up to 30 MHz	8-bit erase and program operations only
V_{DD} = 2.1 to 2.4 V	Conversion time up to 1 Msps	18 MHz with no Flash memory wait state	6(3)	– Degraded speed performance – No I/O compensation	Up to 30 MHz	16-bit erase and program operations
V_{DD} = 2.4 to 2.7 V	Conversion time up to 2 Msps	24 MHz with no Flash memory wait state	4(3)	– Degraded speed performance – I/O compensation works	Up to 48 MHz	16-bit erase and program operations
V_{DD} = 2.7 to 3.6 V(4)	Conversion time up to 2 Msps	30 MHz with no Flash memory wait state	3(3)	– Full-speed operation – I/O compensation works	– Up to 60 MHz when V_{DD} = 3.0 to 3.6 V – Up to 48 MHz when V_{DD} = 2.7 to 3.0 V	32-bit erase and program operations

1. The number of wait states can be reduced by reducing the CPU frequency (see *Figure 21*).
2. On devices in WLCSP64+2 package, if IRROFF is set to V_{DD}, the supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor (see *Section 3.16*).
3. Thanks to the ART accelerator and the 128-bit Flash memory, the number of wait states given here does not impact the execution speed from Flash memory since the ART accelerator allows to achieve a performance equivalent to 0 wait state program execution.
4. The voltage range for OTG USB FS can drop down to 2.7 V. However it is degraded between 2.7 and 3 V.

Figure 21. Number of wait states versus f_{CPU} and V_{DD} range

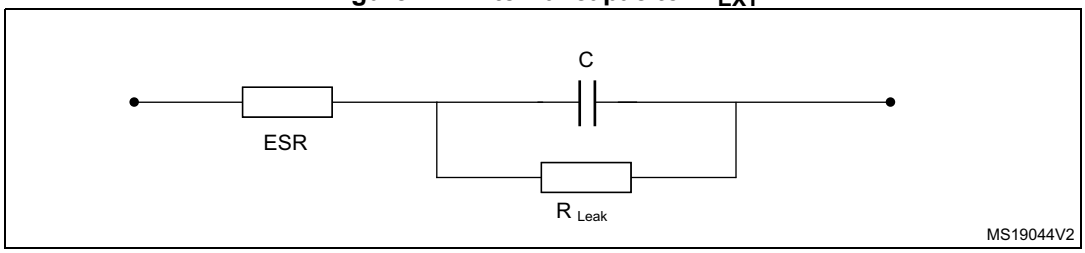


1. The supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range and IRROFF is set to V_{DD}.

6.3.2 VCAP1/VCAP2 external capacitor

Stabilization for the main regulator is achieved by connecting an external capacitor to the VCAP1/VCAP2 pins. C_{EXT} is specified in *Table 16*.

Figure 22. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance.

Table 16. VCAP1/VCAP2 operating conditions(1)

Symbol	Parameter	Conditions
CEXT	Capacitance of external capacitor	2.2 µF
ESR	ESR of external capacitor	< 2 Ω

1. When bypassing the voltage regulator, the two 2.2 µF V_{CAP} capacitors are not required and should be replaced by two 100 nF decoupling capacitors.

6.3.3 Operating conditions at power-up / power-down (regulator ON)

Subject to general operating conditions for T_A.

Table 17. Operating conditions at power-up / power-down (regulator ON)

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	20	∞	µs/V
	V_{DD} fall time rate	20	∞	

6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A.

Table 18. Operating conditions at power-up / power-down (regulator OFF)

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	µs/V
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

Figure 36 and *Figure 37* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 36. PLL output clock waveforms in center spread mode

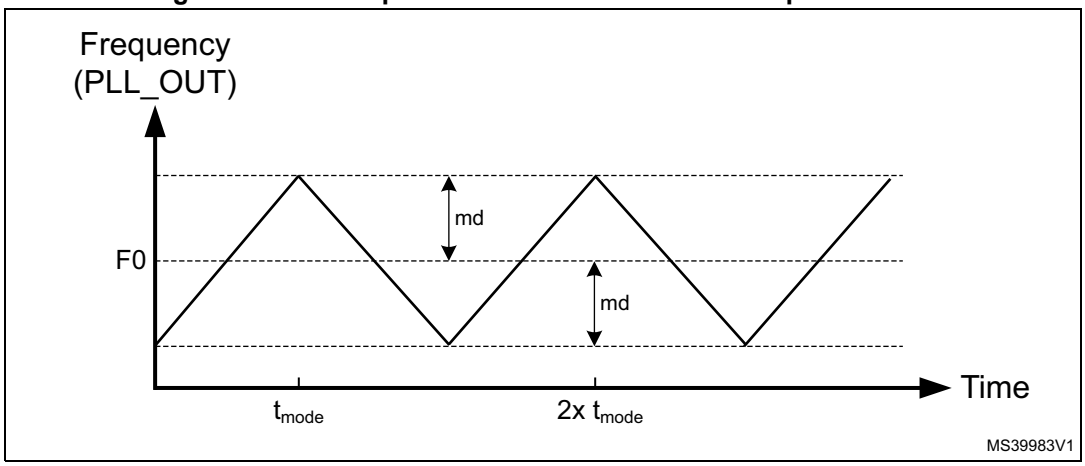
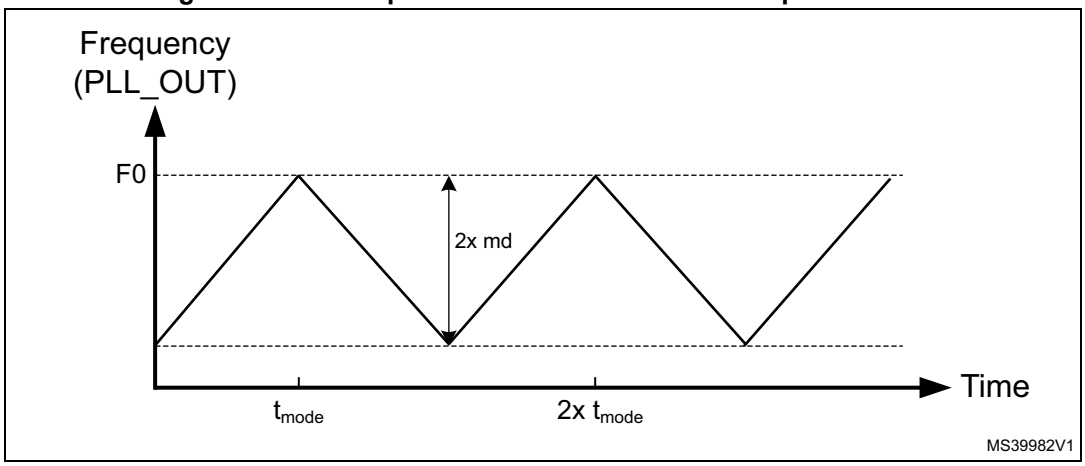


Figure 37. PLL output clock waveforms in down spread mode

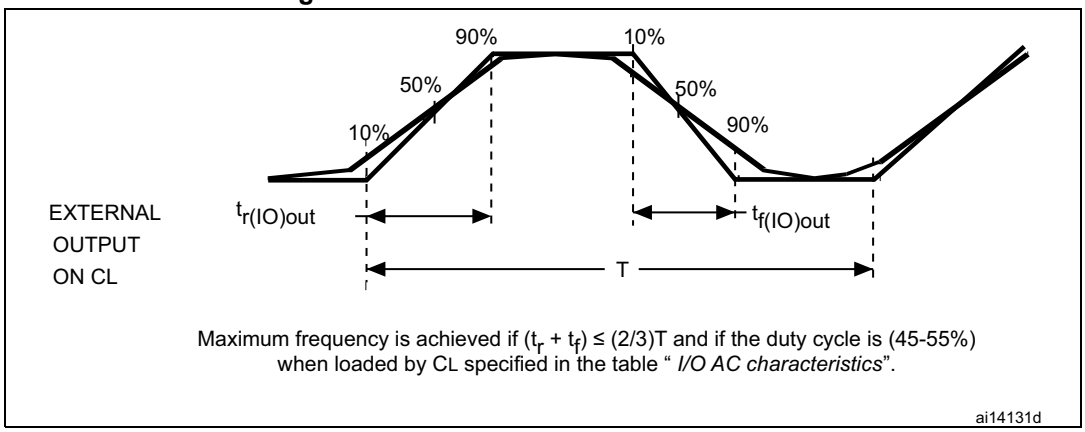


6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Figure 39. I/O AC characteristics definition



6.3.17 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 49*).

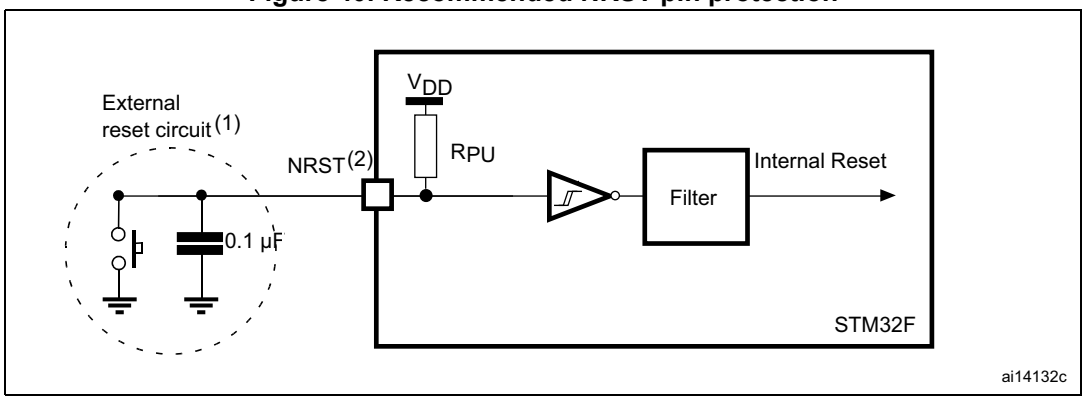
Unless otherwise specified, the parameters given in *Table 49* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 49. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor(1)	$V_{IN} = V_{SS}$	30	40	50	kΩ
$V_{F(NRST)}$(2)	NRST Input filtered pulse	-	-	-	100	ns
$V_{NF(NRST)}$(2)	NRST Input not filtered pulse	V_{DD} > 2.7 V	300	-	-	ns
T_{NRST_OUT}	Generated reset pulse duration	Internal Reset source	20	-	-	µs

1. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).
2. Guaranteed by design, not tested in production.

Figure 40. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 49*. Otherwise the reset is not taken into account by the device.

USB OTG FS characteristics

The USB OTG interface is USB-IF certified (Full-Speed). This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 56. USB OTG FS startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB OTG FS transceiver startup time	1	µs

1. Guaranteed by design, not tested in production.

Table 57. USB OTG FS DC electrical characteristics

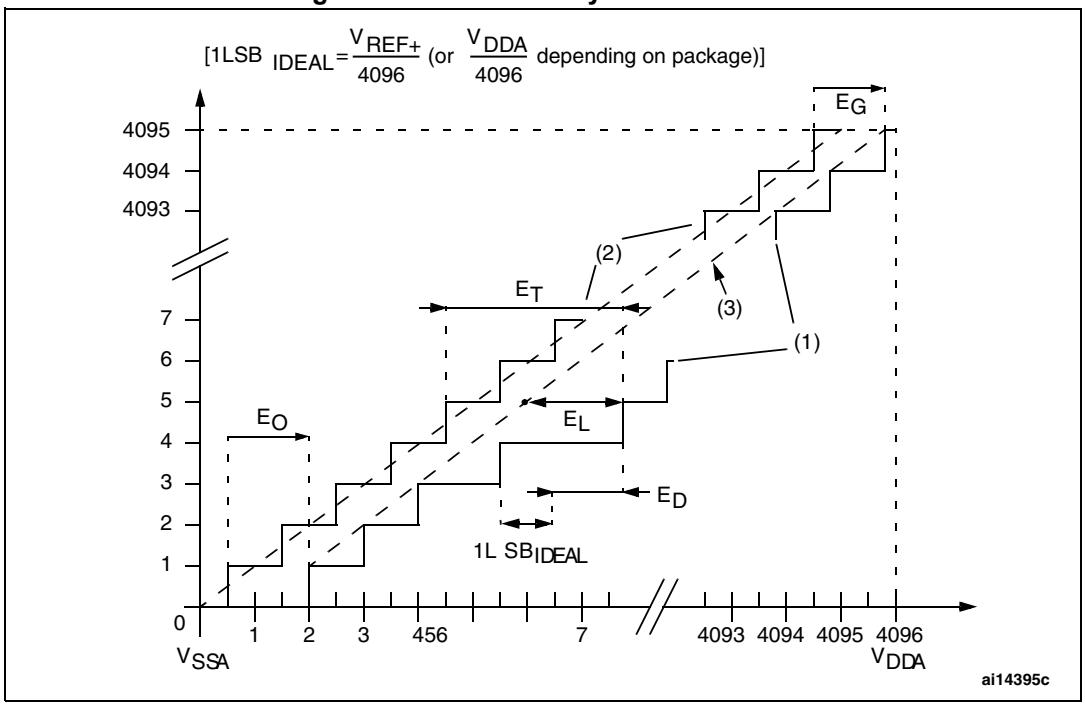
Symbol		Parameter	Conditions	Min.(1)	Typ.	Max.(1)	Unit
Input levels	V_{DD}	USB OTG FS operating voltage		3.0(2)	-	3.6	V
	V_{DI}(3)	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	V
	V_{CM}(3)	Differential common mode range	Includes V_{DI} range	0.8	-	2.5	
	V_{SE}(3)	Single ended receiver threshold		1.3	-	2.0	
Output levels	V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(4)	-	-	0.3	V
	V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(4)	2.8	-	3.6	
R_{PD}		PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	$V_{IN} = V_{DD}$	17	21	24	kΩ
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0	
R_{PU}		PA12, PB15 (USB_FS_DP, USB_HS_DP)	$V_{IN} = V_{SS}$	1.5	1.8	2.1	
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	$V_{IN} = V_{SS}$	0.25	0.37	0.55	

1. All the voltages are measured from the local ground potential.
2. The STM32F205xx and STM32F207xx USB OTG FS functionality is ensured down to 2.7 V but not the full USB OTG FS electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design, not tested in production.
4. R_L is the load connected on the USB OTG FS drivers

being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

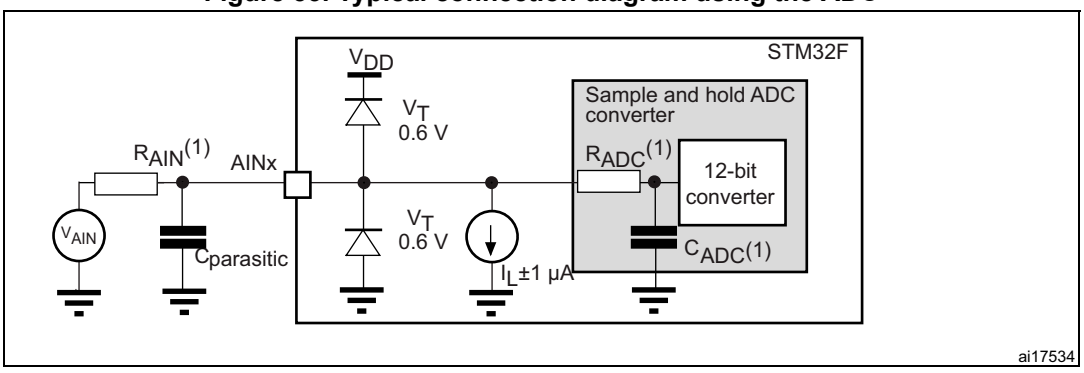
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.16* does not affect the ADC accuracy.

Figure 52. ADC accuracy characteristics



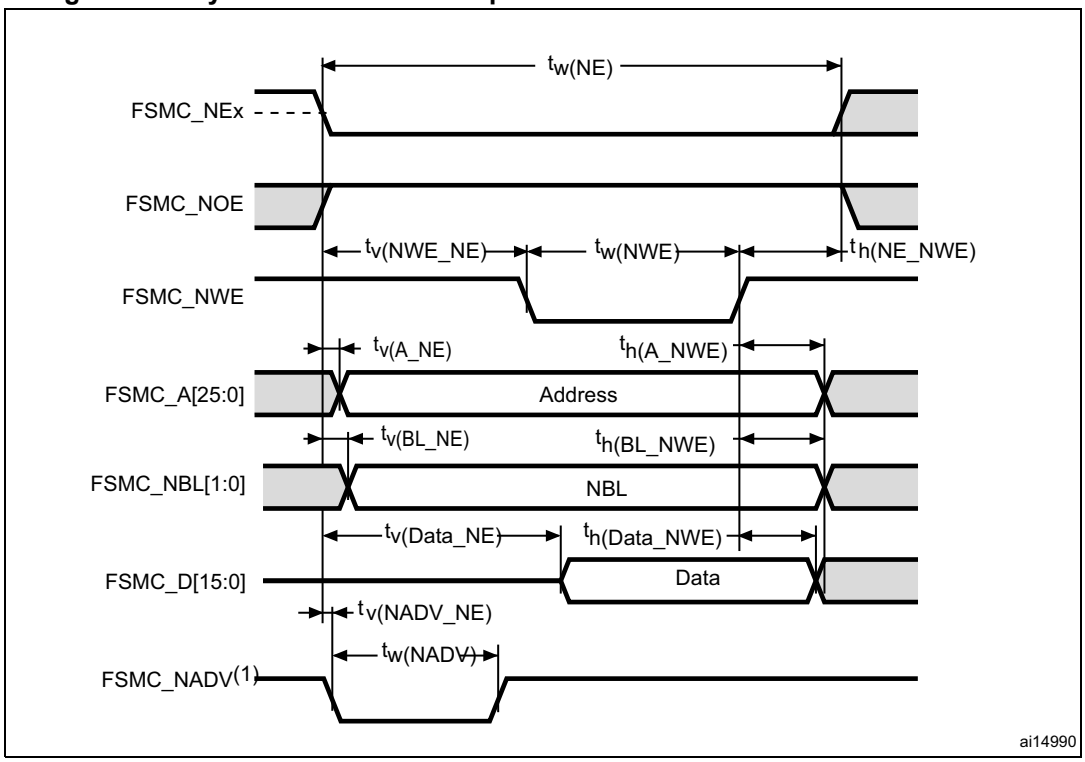
1. Example of an actual transfer curve.
2. Ideal transfer curve.
3. End point correlation line.
4. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 53. Typical connection diagram using the ADC



1. Refer to *Table 66* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

Figure 58. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms



1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

Table 73. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3T_{HCLK}$	$3T_{HCLK}+4$	ns
$t_{v(NWE\_NE)}$	FSMC_NEx low to FSMC_NWE low	$T_{HCLK}-0.5$	$T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FSMC_NWE low time	$T_{HCLK}-0.5$	$T_{HCLK}+3$	ns
$t_{h(NE\_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	T_{HCLK}	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	0	ns
$t_{h(A\_NWE)}$	Address hold time after FSMC_NWE high	$T_{HCLK}-3$	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0.5	ns
$t_{h(BL\_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$T_{HCLK}-1$	-	ns
$t_{v(Data\_NE)}$	Data to FSMC_NEx low to Data valid	-	$T_{HCLK}+5$	ns
$t_{h(Data\_NWE)}$	Data hold time after FSMC_NWE high	$T_{HCLK}+0.5$	-	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	-	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	-	$T_{HCLK}+1.5$	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results, not tested in production.

Figure 59. Asynchronous multiplexed PSRAM/NOR read waveforms

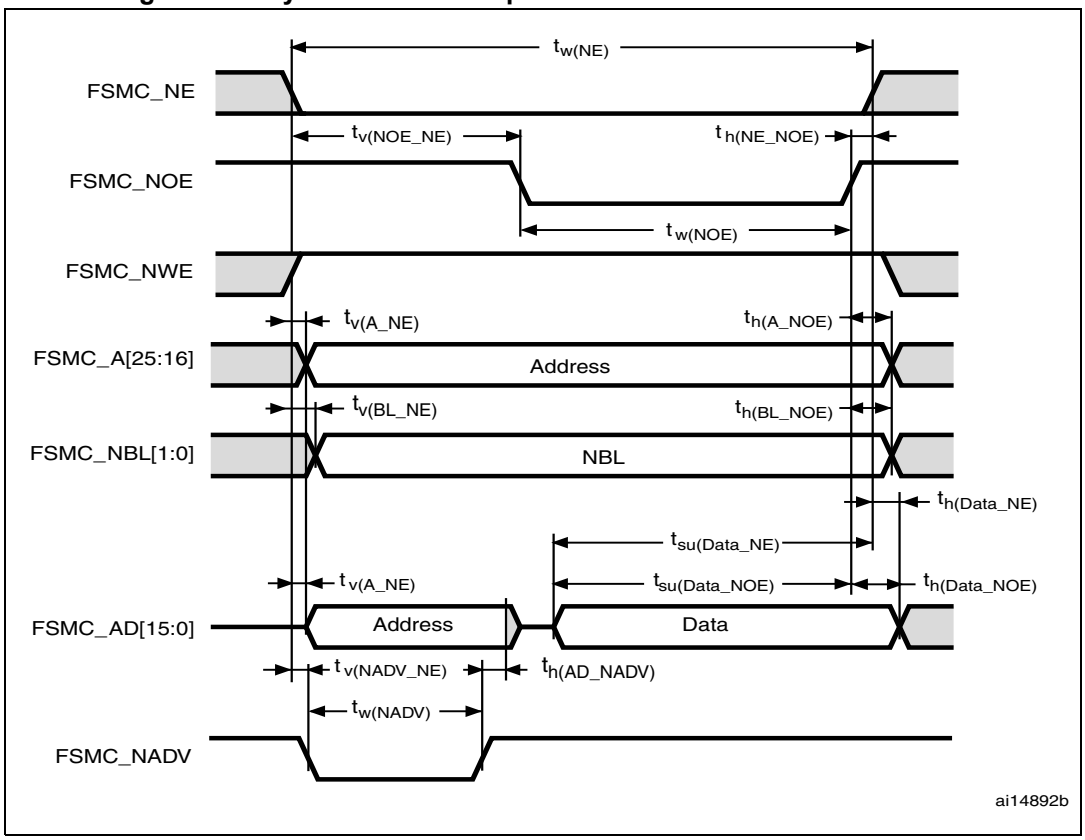
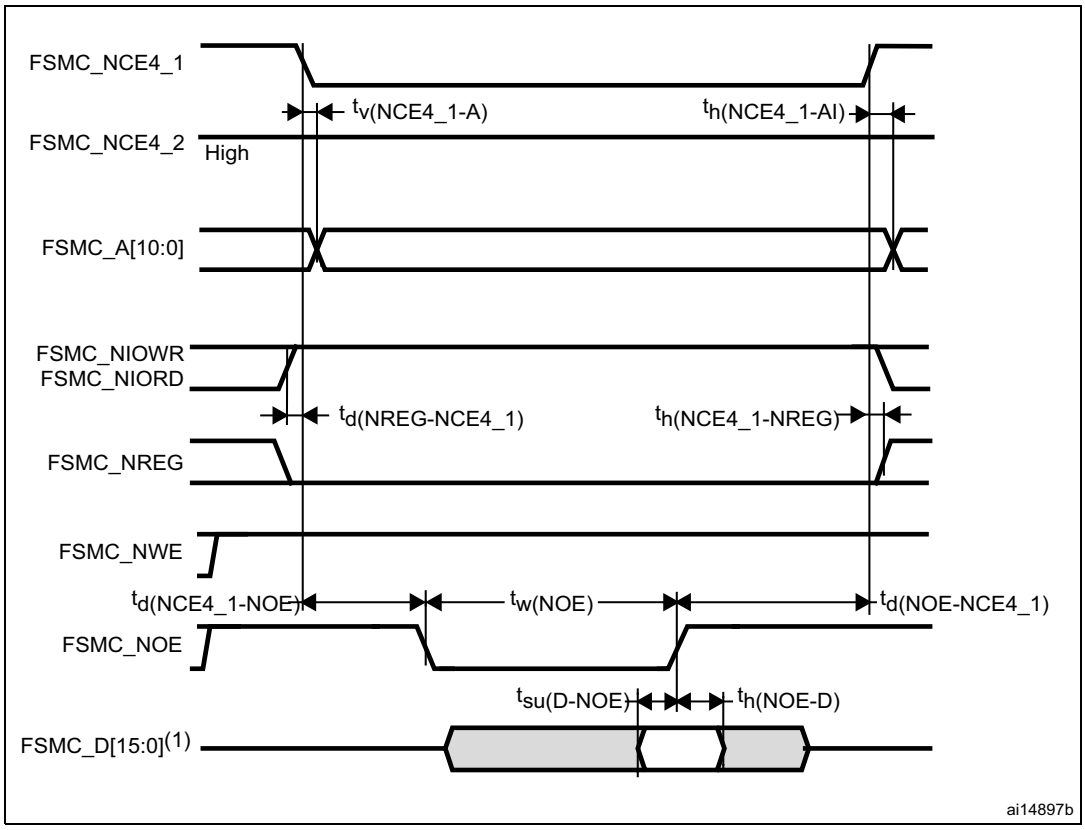


Table 74. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

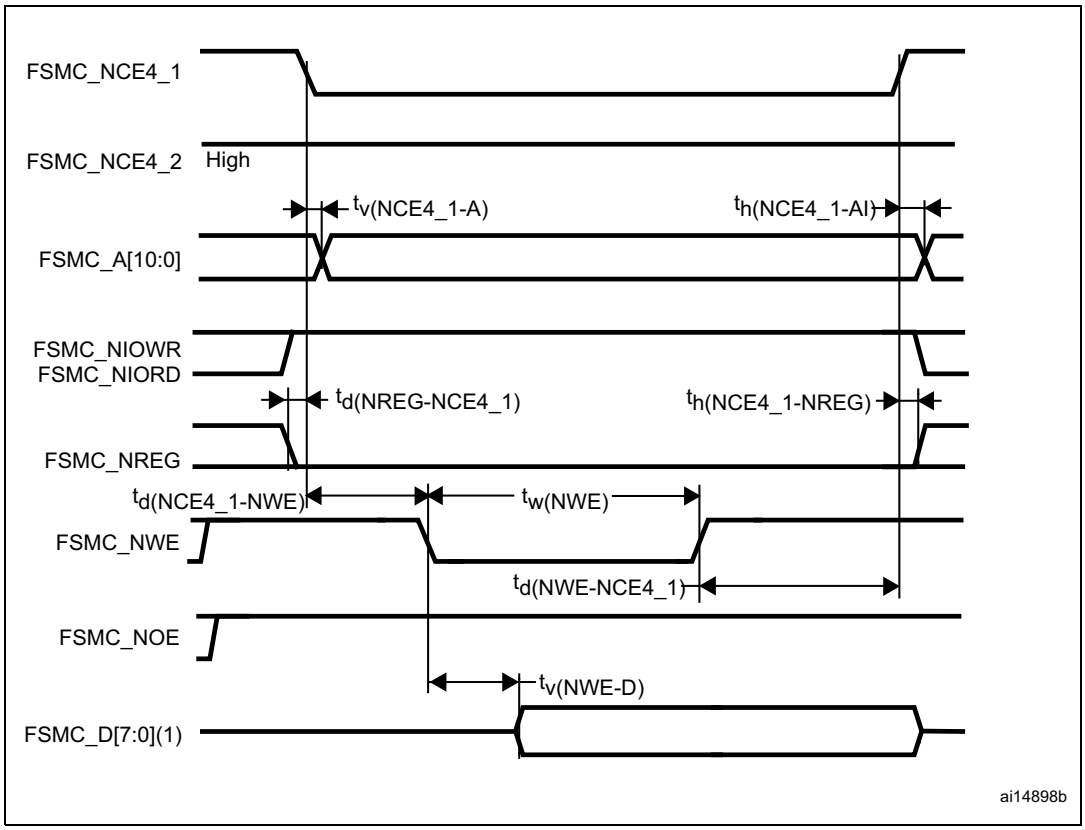
Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3T_{HCLK}$-1	$3T_{HCLK}$+1	ns
$t_{v(NOE\_NE)}$	FSMC_NEx low to FSMC_NOE low	$2T_{HCLK}$	$2T_{HCLK}$+0.5	ns
$t_{w(NOE)}$	FSMC_NOE low time	T_{HCLK}-1	T_{HCLK}+1	ns
$t_{h(NE\_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	2	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	1	2.5	ns
$t_{w(NADV)}$	FSMC_NADV low time	T_{HCLK}– 1.5	T_{HCLK}	ns
$t_{h(AD\_NADV)}$	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T_{HCLK}	-	ns
$t_{h(A\_NOE)}$	Address hold time after FSMC_NOE high	T_{HCLK}	-	ns
$t_{h(BL\_NOE)}$	FSMC_BL time after FSMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	1	ns
$t_{su(Data\_NE)}$	Data to FSMC_NEx high setup time	T_{HCLK}+ 2	-	ns
$t_{su(Data\_NOE)}$	Data to FSMC_NOE high setup time	T_{HCLK}+ 3	-	ns

Figure 67. PC Card/CompactFlash controller waveforms for attribute memory read access



1. Only data bits 0...7 are read (bits 8...15 are disregarded).

Figure 68. PC Card/CompactFlash controller waveforms for attribute memory write access



1. Only data bits 0...7 are driven (bits 8...15 remains Hi-Z).

Figure 69. PC Card/CompactFlash controller waveforms for I/O space read access

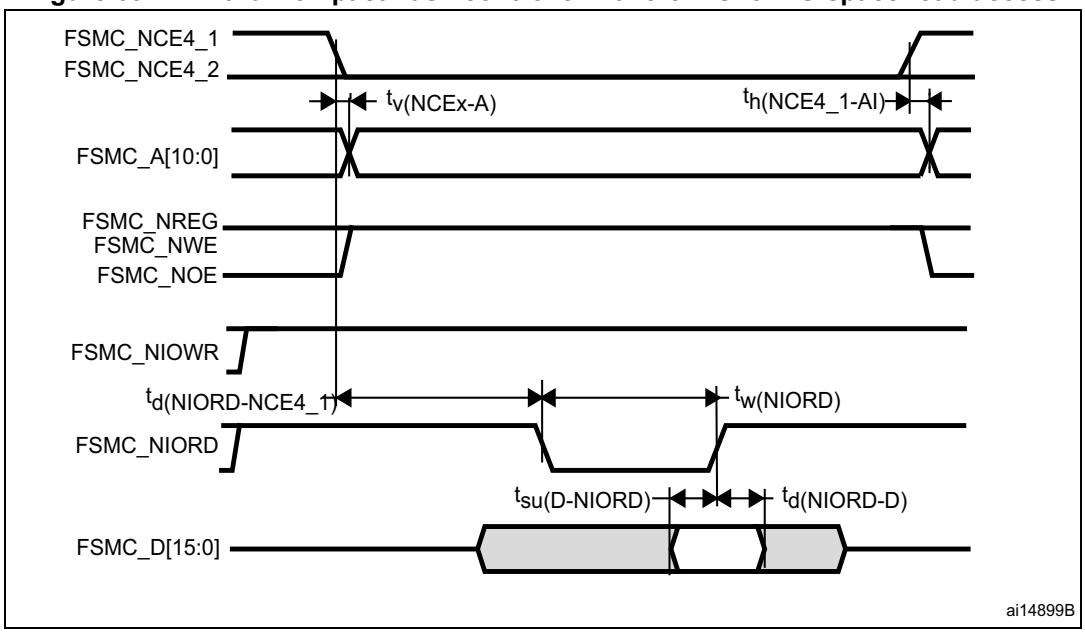


Figure 70. PC Card/CompactFlash controller waveforms for I/O space write access

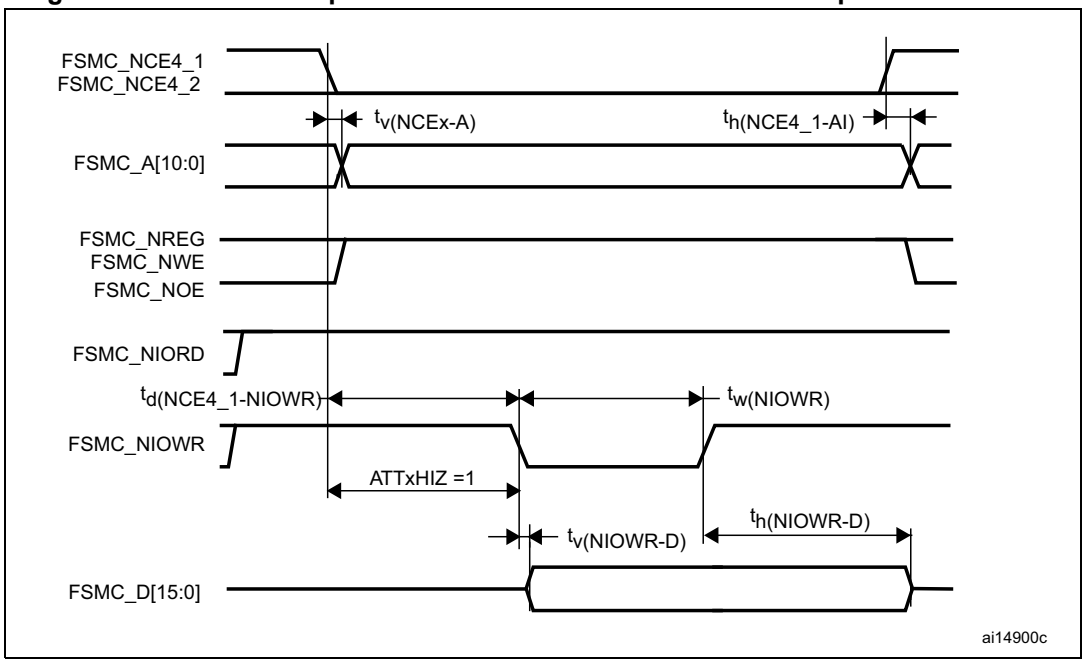


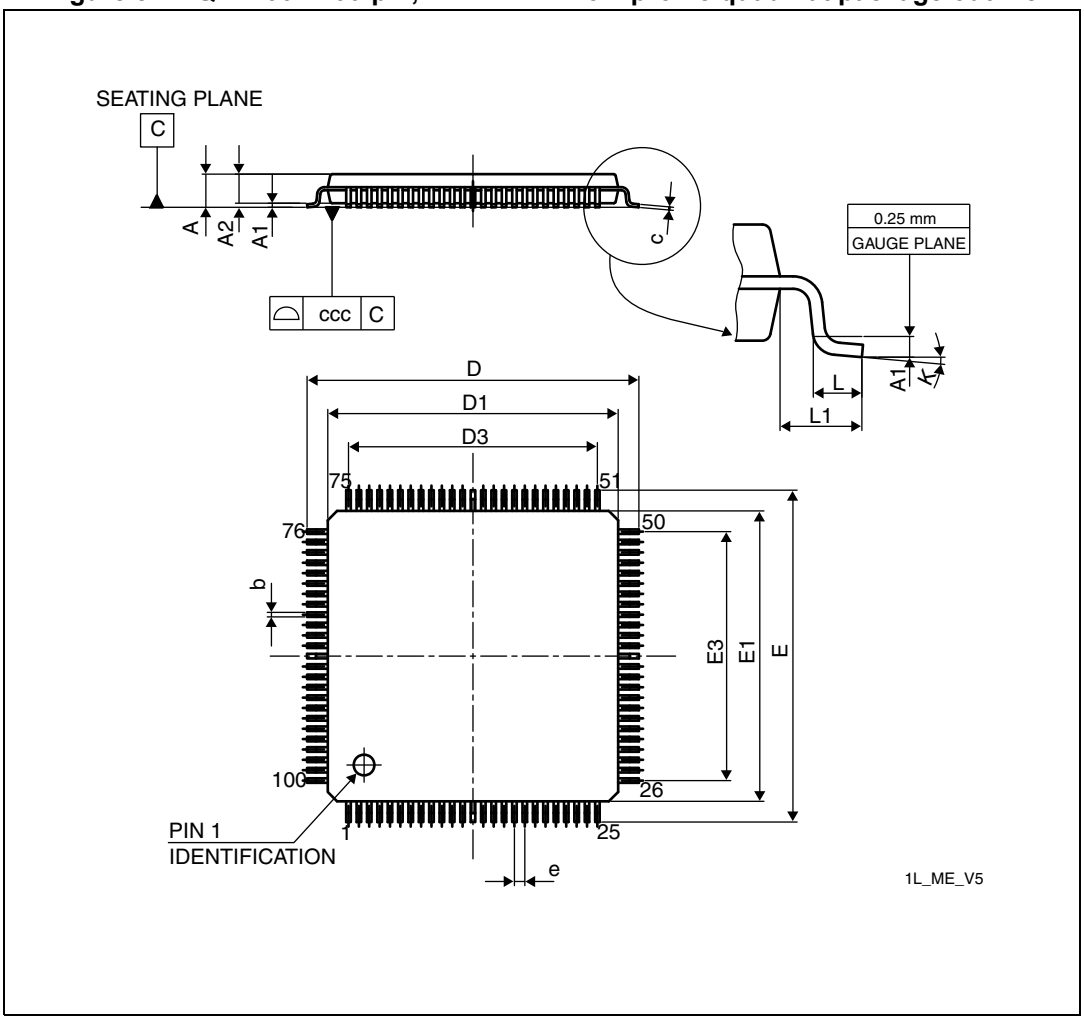
Table 80. Switching characteristics for PC Card/CF read and write cycles in attribute/common space(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$	FSMC_Ncex low to FSMC_Ay valid	-	0	ns
$t_{h(NCEx\_AI)}$	FSMC_NCEx high to FSMC_Ax invalid	4	-	ns
$t_{d(NREG-NCEx)}$	FSMC_NCEx low to FSMC_NREG valid	-	3.5	ns
$t_{h(NCEx-NREG)}$	FSMC_NCEx high to FSMC_NREG invalid	T_{HCLK}+ 4	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	$5T_{HCLK}$+ 1	ns
$t_{d(NCEx-NOE)}$	FSMC_NCEx low to FSMC_NOE low	-	$5T_{HCLK}$	ns
$t_{w(NOE)}$	FSMC_NOE low width	$8T_{HCLK}$– 0.5	$8T_{HCLK}$+ 1	ns
$t_{d(NOE\_NCEx)}$	FSMC_NOE high to FSMC_NCEx high	$5T_{HCLK}$+ 2.5	-	ns
$t_{su\ (D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	4	-	ns
$t_{h\ (N0E-D)}$	FSMC_N0E high to FSMC_D[15:0] invalid	2	-	ns
$t_{w(NWE)}$	FSMC_NWE low width	$8T_{HCLK}$- 1	$8T_{HCLK}$+ 4	ns
$t_{d(NWE\_NCEx)}$	FSMC_NWE high to FSMC_NCEx high	$5T_{HCLK}$+ 1.5	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	5HCLK+ 1	ns
$t_{v\ (NWE-D)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
$t_{h\ (NWE-D)}$	FSMC_NWE high to FSMC_D[15:0] invalid	$8T_{HCLK}$	-	ns
$t_{d\ (D-NWE)}$	FSMC_D[15:0] valid before FSMC_NWE high	$13T_{HCLK}$	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results, not tested in production.

7.3 LQFP100 package information

Figure 81. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline

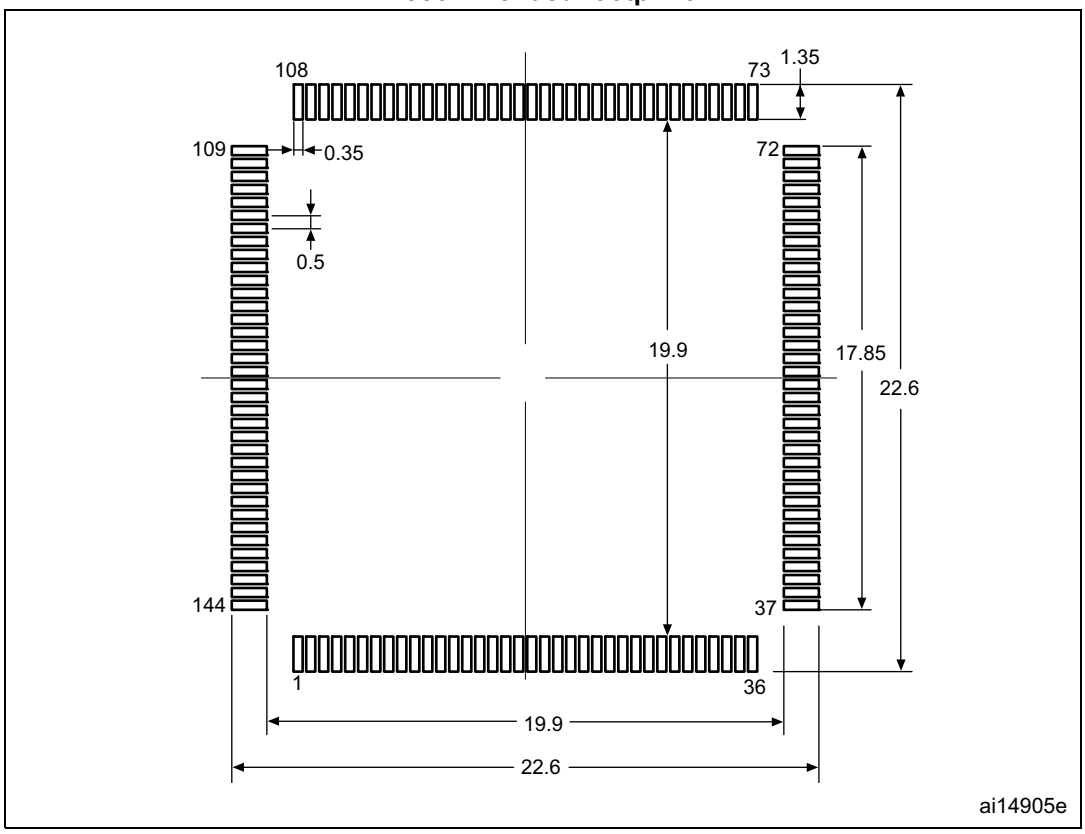


1. Drawing is not to scale.

Table 90. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591

Figure 85. LQFP144 - 144-pin,20 x 20 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Table 97. Document revision history (continued)

Date	Revision	Changes
25-Nov-2010	5	Update I/Os in *Section : Features*. Added WLCSP64+2 package. Added note 1 related to LQFP176 on cover page. Added trademark for ART accelerator. Updated *Section 3.2: Adaptive real-time memory accelerator (ART Accelerator™)*. Updated *Figure 5: Multi-AHB matrix*. Added case of BOR inactivation using IRROFF on WLCSP devices in *Section 3.15: Power supply supervisor*. Reworked *Section 3.16: Voltage regulator* to clarify regulator off modes. Renamed PDROFF, IRROFF in the whole document. Added *Section 3.19: VBAT operation*. Updated LIN and IrDA features for UART4/5 in *Table 6: USART feature comparison*. *Table 8: STM32F20x pin and ball definitions*: Modified V_{DD_3} pin, and added note related to the FSMC_NL pin; renamed BYPASS-REG REGOFF, and add IRROFF pin; renamed USART4/5 UART4/5. USART4 pins renamed UART4. Changed V_{SS_SA} to V_{SS}, and V_{DD_SA} pin reserved for future use. Updated maximum HSE crystal frequency to 26 MHz. *Section 6.2: Absolute maximum ratings*: Updated V_{IN} minimum and maximum values and note related to five-volt tolerant inputs in *Table 11: Voltage characteristics*. Updated $I_{INJ(PIN)}$ maximum values and related notes in *Table 12: Current characteristics*. Updated V_{DDA} minimum value in *Table 14: General operating conditions*. Added Note 2 and updated Maximum CPU frequency in *Table 15: Limitations depending on the operating power supply range*, and added *Figure 21: Number of wait states versus fCPU and VDD range*. Added brownout level 1, 2, and 3 thresholds in *Table 19: Embedded reset and power control block characteristics*. Changed f_{OSC_IN} maximum value in *Table 30: HSE 4-26 MHz oscillator characteristics*. Changed f_{PLL_IN} maximum value in *Table 34: Main PLL characteristics*, and updated jitter parameters in *Table 35: PLLI2S (audio PLL) characteristics*. *Section 6.3.16: I/O port characteristics*: updated V_{IH} and V_{IL} in *Table 48: I/O AC characteristics*. Added *Note 1* below *Table 47: Output voltage characteristics*. Updated R_{PD} and R_{PU} parameter description in *Table 57: USB OTG FS DC electrical characteristics*. Updated V_{REF+} minimum value in *Table 66: ADC characteristics*. Updated *Table 71: Embedded internal reference voltage*. Removed Ethernet and USB2 for 64-pin devices in *Table 101: Main applications versus package for STM32F2xxx microcontrollers*. Added *A.2: USB OTG full speed (FS) interface solutions*, removed “OTG FS connection with external PHY” figure, updated *Figure 87*, *Figure 88*, and *Figure 90* to add STULPI01B.

Table 97. Document revision history (continued)

Date	Revision	Changes
14-Jun-2011	7	Added SDIO in *Table 2: STM32F205xx features and peripheral counts*. Updated V_{IN} for 5V tolerant pins in *Table 11: Voltage characteristics*. Updated jitter parameters description in *Table 34: Main PLL characteristics*. Remove jitter values for system clock in *Table 35: PLLI2S (audio PLL) characteristics*. Updated *Table 42: EMI characteristics*. Update *Note 2* in *Table 52: I2C characteristics*. Updated Avg_Slope typical value and T_{S_temp} minimum value in *Table 69: Temperature sensor characteristics*. Updated T_{S_vbat} minimum value in *Table 70: VBAT monitoring characteristics*. Updated $T_{S\_vrefint}$ minimum value in *Table 71: Embedded internal reference voltage*. Added Software option in *Section 8: Part numbering*. In *Table 101: Main applications versus package for STM32F2xxx microcontrollers*, renamed USB1 and USB2, USB OTG FS and USB OTG HS, respectively; and removed USB OTG FS and camera interface for 64-pin package; added USB OTG HS on 64-pin package; added *Note 1* and *Note 2*.
20-Dec-2011	8	Updated SDIO register addresses in *Figure 16: Memory map*. Updated *Figure 3: Compatible board design between STM32F10xx and STM32F2xx for LQFP144 package*, *Figure 2: Compatible board design between STM32F10xx and STM32F2xx for LQFP100 package*, *Figure 1: Compatible board design between STM32F10xx and STM32F2xx for LQFP64 package*, and added *Figure 4: Compatible board design between STM32F10xx and STM32F2xx for LQFP176 package*. Updated *Section 3.3: Memory protection unit*. Updated *Section 3.6: Embedded SRAM*. Updated *Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS)* to remove external FS OTG PHY support. In *Table 8: STM32F20x pin and ball definitions*: changed SPI2_MCK and SPI3_MCK to I2S2_MCK and I2S3_MCK, respectively. Added ETH _RMII_TX_EN atlternate function to PG11. Added EVENTOUT in the list of alternate functions for I/O pin/balls. Removed OTG_FS_SDA, OTG_FS_SCL and OTG_FS_INTN alternate functions. In *Table 10: Alternate function mapping*: changed I2S3_SCK to I2S3_MCK for PC7/AF6, added FSMC_NCE3 for PG9, FSMC_NE3 for PG10, and FSMC_NCE2 for PD7. Removed OTG_FS_SDA, OTG_FS_SCL and OTG_FS_INTN alternate functions. Changed I2S3_SCK into I2S3_MCK for PC7/AF6. Updated peripherals corresponding to AF12. Removed CEXT and ESR from *Table 14: General operating conditions*.

Table 97. Document revision history (continued)

Date	Revision	Changes
24-Apr-2012	9 (continued)	Removed support of I2C for OTG PHY in *Section 3.29: Universal serial bus on-the-go high-speed (OTG_HS)*. Removed OTG_HS_SCL, OTG_HS_SDA, OTG_FS_INTN in *Table 8: STM32F20x pin and ball definitions* and *Table 10: Alternate function mapping*. Renamed PH10 alternate function into TIM5_CH1 in *Table 10: Alternate function mapping*. Added *Table 9: FSMC pin definition*. Updated *Note 1* in *Table 14: General operating conditions*, *Note 2* in *Table 15: Limitations depending on the operating power supply range*, and *Note 1* below *Figure 21: Number of wait states versus fCPU and VDD range*. Updated $V_{POR/PDR}$ in *Table 19: Embedded reset and power control block characteristics*. Updated typical values in *Table 24: Typical and maximum current consumptions in Standby mode* and *Table 25: Typical and maximum current consumptions in VBAT mode*. Updated *Table 30: HSE 4-26 MHz oscillator characteristics* and *Table 31: LSE oscillator characteristics (fLSE = 32.768 kHz)*. Updated *Table 37: Flash memory characteristics*, *Table 38: Flash memory programming*, and *Table 39: Flash memory programming with VPP*. Updated *Section : Output driving current*. Updated *Note 3* and removed note related to minimum hold time value in *Table 52: I2C characteristics*. Updated *Table 64: Dynamics characteristics: Ethernet MAC signals for RMII*. Updated *Note 1*, C_{ADC}, I_{VREF+}, and I_{VDDA} in *Table 66: ADC characteristics*. Updated *Note 3* and note concerning ADC accuracy vs. negative injection current in *Table 67: ADC accuracy*. Updated *Note 1* in *Table 68: DAC characteristics*. Updated *Section Figure 88.: UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm, package outline*. Appendix *A.1: Main applications versus package*: removed number of address lines for FSMC/NAND in *Table 101: Main applications versus package for STM32F2xxx microcontrollers*. Appendix *A.4: Ethernet interface solutions*: updated *Figure 92: Complete audio player solution 1* and *Figure 93: Complete audio player solution 2*.